

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (DARLINGTON POWER TRANSISTOR)

2SD2384

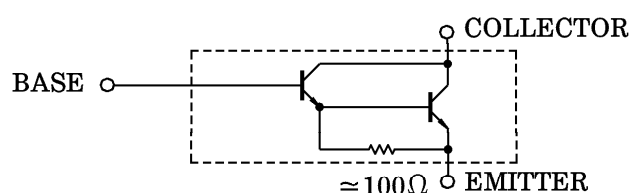
POWER AMPLIFIER APPLICATIONS

- High Breakdown Voltage : $V_{CEO}=140\text{V}$ (Min.)
- Complementary to 2SB1555

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	140	V
Collector-Emitter Voltage	V_{CEO}	140	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	7	A
Base Current	I_B	0.1	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	100	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

EQUIVALENT CIRCUIT



Unit in mm

JEDEC	—
EIAJ	—
TOSHIBA	2-21F1A

ELECTRICAL CHARACTERISTIC ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB}=140\text{V}$, $I_E=0$	—	—	5.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$	—	—	5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50\text{mA}$, $I_B=0$	140	—	—	V
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE}=5\text{V}$, $I_C=6\text{A}$	5000	—	30000	—
	$h_{FE}(2)$	$V_{CE}=5\text{V}$, $I_C=10\text{A}$	2000	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=6\text{A}$, $I_B=6\text{mA}$	—	—	2.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5\text{V}$, $I_C=6\text{A}$	—	—	3.0	V
Transition Frequency	f_T	$V_{CE}=5\text{V}$, $I_C=1\text{A}$	—	30	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$	—	90	—	pF

Note : $h_{FE}(1)$ Classification A : 5000~12000, B : 9000~18000, C : 15000~30000

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